PCN Numb	er:		202	210325002.2				PCN	Da	te:	Mar 31, 2021	
Title:	Qualif	ication o	f MIH	HO8 as add	itional	Fab Si	te option	for s	elec	t ABC	D05HV devices	
Customer	Customer Contact: PCN Manager Dept: Quality Services											
Proposed 1 st Ship Date:				Sep 30, 2021			Estimated Sample Availability:			ple	Date provided at sample request.	
Change Ty	pe:								-			
	hbly Sit	e		Asse	mbly F	Process			ŀ	Asseml	mbly Materials	
Desigi	n			Elect	rical S	pecifica	ation		1	Mechar	nical Specification	
Test S							'Labeling	g 📃 Test Pr				
	Bump			Wafer Bump Material							Bump Process	
🛛 🛛 Wafer	Fab Si	te		Wafer Fab Materials Wafer Fab Process						Fab Process		
					Part number change Notification Details							
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											cted" section.	
	valeri			the select	eu uev	1003 113			Juu		cied section.	
	Cur	rent Fa	b Sit	te			Α	dditio	ona	l Fab S	Site	
Current I Site	Fab	Proces	s	Wafer Diamet			tional Site	Pr	roce	ess	Wafer Diameter	
MAINEFA	AB	ABCD05	HV	200 mr			108	ABO		5HV	200 mm	
			1				ADCD0511			5111	200 1111	
Qual details	s are pr	rovided i	n the	e Qual Data	Sectio	on.						
Reason fo	r Chan	ge:										
Continuity of	of supp	oly.										
Anticipate	d impa	act on F	it, Fo	orm, Func	tion, (Quality	or Reli	abilit	ty (positi	ve / negative):	
None.												
Changes to product identification resulting from this PCN:												
..												
Current												
Chip Si	ite	Chip S	ite O	rigin (20L)	Chip	ip Site Country Code (21L)			_)	Chip Site City		
MAINEF			CU	JA USA			USA	USA			South Portland	
	, (0						00/1				oodan i ordana	
New Eek	Site											
New Fab Chip Si		Chin S	ito O	rigin (20L)	Chir	a Sita (Country (Code ((21)	1	Chip Site City	
		Chip 3			Cin	J Site C		Loue	(211	-)		
MIHO	8		MH	18			JPN				Ibaraki	
Sample pro	duct ch	inning l	abal	(not actual	nrodu	ct labo	IN IN					
Sample pro	uuct Si	iipping ia	abei		produ)					
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TEXA INSTRUM			(Pb) n ==	₿ de t	3£ (1P) SN	741 \$	\$07	NSR		
MADE IN:		ia	G4		8 . S		(a) 20			(D) ()	336	
MSL 2 /260C/1 YEAR SEAL DT KEALSTAN (31T)LOT: 3959047MLA												
MSL 1 /235C/UNLIM 03/29/04 100 100 100 100 100 100 100 100 100 1												
OPT: ITEM: 39												
LBL: 5A (L)T0:1750												

Product Affected:								
LM3492AHCQMH/NOPB	LM3492EHCQMH	LM3492HCQMH/NOPB	LM3492HCQMHX/NOPB					
LM3492AHCQMHX/NOPB	LM3492EHCQMHX							

Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Approve Date 29-December-2020

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре									
		Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: LM3492HCQMHX/NOPB	QBS Process/Package Device: LM25117QPMHX/NOPB	QBS Process Reference TCAN1042HVDRQ1
Test Gro	A – A qu	ccelerated Environmer	nt Stres	is Test	5				
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	-	3/231/0	3/231/0
AC	A3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 Hours	-	3/231/0	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	-	3/231/0	3/231/0
TC-BI	P A4	MIL-STD883 Method 2011	1	30	Post Temp. Cycle Bond Pull	Wires	-	1/30/0	1/30/0
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle	1000 Cycles	-	N/A	NA
HTSI	A6	JEDEC JESD22- A103	1	45	High Temp. Storage Bake, 150C	1000 Hours	-	1/45/0	1/45/0
Test Gro	ıр В – А	ccelerated Lifetime Sir	nulatio	n Tests	i				
нто	B1	JEDEC JESD22- A108	3	77	Life Test, 125C	1000 Hours	-	3/231/1 (Note 1)	3/231/0
ELFF	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	-	-	3/2400/0
Test Gro	ю С – Р	ackage Assembly Integ	arity Te	sts					
WBS		AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	1/30/0	1/30/0	1/30/0
WBF	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	1/30/0	1/30/0
SD	СЗ	JEDEC JESD22- B102	1	15	Solderability (>95% Lead Coverage)	Pb & Pb-Free	N/A	N/A	N/A
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	N/A	N/A	N/A
Test Gro	ıp D – D	ie Fabrication Reliabili	ty Test	5					
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDE	D2	JESD35	-	-	Time Dependant Dielectric Breakdown		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBT	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Gro	10 E – E	lectrical Verification Te	sts						
HBM	•	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	1/3/0	1/3/0
CDM		AEC Q100-011	1	3	ESD - CDM	750 V	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, Hot, & Cold Test	1/30/0	3/90/0	3/90/0

Qual Device LM3492HCQMHX/NOPB is qualified at LEVEL1-260C A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable. Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C

Grade 3 (or I) : -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

Note 1: 1 discounted fail that occurred at 168 hrs has been attributed to EOS most likely caused by handling issues. FA report attached to eQDB.

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
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